Taizoh Sadoh

List of Publications by Year in Descending Order

191 papers	2,633 citations	29 h-index	42 g-index
236 ext. papers	2,844 ext. citations	2.2 avg, IF	4.8 L-index

#	Paper	IF	Citations
191	Fabrication of CMOS Invertors in Si Thin-Film-Transistors by Laser Doping Using a Chemical Solution Coating. *IEEE Journal of the Electron Devices Society*, **2020**, 8, 27-32	2.3	1
190	Layer-exchange crystallization for low-temperature (~450 ℃) formation of n-type tensile-strained Ge on insulator. *Applied Physics Letters*, **2020**, 117, 172102	3.4	1
189	High mobility sputtered InSb film by blue laser diode annealing. *AIP Advances*, **2019**, 9, 045009	1.5	1
188	Enhanced mobility of Sn-doped Ge thin-films (≦50 nm) on insulator for fully depleted transistors by nucleation-controlled solid-phase crystallization. *Applied Physics Letters*, **2019**, 115, 042101	3.4	9
187	Low-Temperature (~250℃) Gold-Induced Lateral Growth of Sn-Doped Ge on Insulator Enhanced by Layer-Exchange Reaction. *ECS Journal of Solid State Science and Technology*, **2019**, 8, P609-P614	2	
186	Nucleation-controlled low-temperature solid-phase crystallization for Sn-doped polycrystalline-Ge film on insulator with high carrier mobility (~550 cm2/V s). *Applied Physics Letters*, **2018**, 112, 242103	3.4	1
185	Large single-crystal Ge-on-insulator by thermally-assisted (~400 ℃) Si-seeded-pulse-laser annealing. *Materials Science in Semiconductor Processing*, **2017**, 70, 8-11	4.3	2
184	30-4: Characterization of Si Thin Films Doped by Wet-Chemical Laser Processing. *Digest of Technical Papers SID International Symposium*, **2017**, 48, 430-432	0.5	1
183	Low-temperature (. *AIP Advances*, **2017**, 7, 075204	1.5	1
182	Novel growth techniques of group-IV based semiconductors on insulator for next-generation electronics. *Japanese Journal of Applied Physics*, **2017**, 56, 05DA06	1.4	19
181	Quasi-single crystal SiGe on insulator by Au-induced crystallization for flexible electronics. *Japanese Journal of Applied Physics*, **2016**, 55, 03CB01	1.4	12
180	(Invited) Low-Temperature Growth of Orientation-Controlled Large-Grain Ge-Rich SiGe on Insulator at Controlled-Position for Flexible Electronics. *ECS Transactions*, **2016**, 75, 95-103	1	
179	High Sn-concentration (~8%) GeSn by low-temperature (~150℃) solid-phase epitaxy of a-GeSn/c-Ge. *Thin Solid Films*, **2016**, 602, 20-23	2.2	5
178	Formation of germanium (111) on graphene on insulator by rapid melting growth for novel germanium-on-insulator structure. *Materials Letters*, **2016**, 168, 223-227	3.3	3
177	Seeding Effects of Sn/a-Ge Island Structures for Low-Temperature Lateral-Growth of a-GeSn on Insulator. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P76-P79	2	
176	Low-Temperature Formation of Large-Grain (□10 □m) Ge at Controlled-Position on Insulator by Gold-Induced Crystallization Combined with Diffusion-Barrier Patterning. *ECS Journal of Solid State Science and Technology*, **2016**, 5, P179-P182	2	4
175	Low-temperature (≦300℃) formation of orientation-controlled large-grain (□10□m) Ge-rich SiGe on insulator by gold-induced crystallization. *Thin Solid Films*, **2016**, 602, 3-6	2.2	2

174	High carrier mobility of Sn-doped polycrystalline-Ge films on insulators by thickness-dependent low-temperature solid-phase crystallization. *Applied Physics Letters*, **2016**, 109, 232106	3.4	31
173	Pulse number controlled laser annealing for GeSn on insulator structure with high substitutional Sn concentration. *Applied Physics Letters*, **2016**, 108, 262105	3.4	13
172	Formation of large-grain crystalline germanium on single layer graphene on insulator by rapid melting growth. *Materials Letters*, **2016**, 178, 147-150	3.3	
171	Thickness Dependent Solid-Phase Crystallization of Amorphous GeSn on Insulating Substrates at Low Temperatures (. *ECS Solid State Letters*, **2015**, 4, P95-P97		5
170	Ultra-low temperature (300 °C) growth of Ge-rich SiGe by solid-liquid-coexisting annealing of a-GeSn/c-Si structures. *Journal of Applied Physics*, **2015**, 118, 095707	2.5	4
169	High quality, giant crystalline-Ge stripes on insulating substrate by rapid-thermal-annealing of Sn-doped amorphous-Ge in solid-liquid coexisting region. *AIP Advances*, **2015**, 5, 067112	1.5	2
168	(Invited) Gold-Induced Low-Temperature (. *ECS Transactions*, **2015**, 69, 21-27	1	
167	Low-temperature (~180 °C) position-controlled lateral solid-phase crystallization of GeSn with laser-anneal seeding. *Applied Physics Letters*, **2015**, 107, 262106	3.4	15
166	Coherent lateral-growth of Ge over insulating film by rapid-melting-crystallization. *Thin Solid Films*, **2014**, 557, 135-138	2.2	1
165	Sn-induced low-temperature (~ 150 °C) crystallization of Ge on insulator. *Thin Solid Films*, **2014**, 557, 155-158	2.2	3
164	In-depth analysis of high-quality Ge-on-insulator structure formed by rapid-melting growth. *Thin Solid Films*, **2014**, 557, 139-142	2.2	3
163	Dynamic analysis of rapid-melting growth using SiGe on insulator. *Thin Solid Films*, **2014**, 557, 125-128	2.2	
162	Formation of Large Grain Ge Single Crystal on Insulating Substrate by Liquid-Solid Coexisting Annealing of a-Ge(Sn). *ECS Transactions*, **2014**, 61, 97-100	1	
161	Giant-Lateral-Growth of SiGe Stripes on Insulating-Substrate by Self-Organized-Seeding and Rapid-Melting-Growth in Solid-Liquid Coexisting Region. *ECS Solid State Letters*, **2014**, 3, P61-P64		6
160	The Effects of Annealing Temperatures on Composition and Strain in SiGe Obtained by Melting Growth of Electrodeposited Ge on Si (100). *Materials*, **2014**, 7, 1409-1421	3.5	5
159	Ultra-high-speed lateral solid phase crystallization of GeSn on insulator combined with Sn-melting-induced seeding. *Applied Physics Letters*, **2014**, 105, 202112	3.4	24
158	High carrier mobility in orientation-controlled large-grain (50 μm) Ge directly formed on flexible plastic by nucleation-controlled gold-induced-crystallization. *Applied Physics Letters*, **2014**, 104, 252110	3.4	61
157	Comprehensive study of Al-induced layer-exchange growth for orientation-controlled Si crystals on SiO2 substrates. *Journal of Applied Physics*, **2014**, 116, 173510	2.5	37

156	Large-grain SiGe-on-insulator with uniform Si concentration by segregation-free rapid-melting growth. *Applied Physics Letters*, **2014**, 105, 102106	3.4	9
155	(111)-oriented large-grain (50 μm) Ge crystals directly formed on flexible plastic substrate by gold-induced layer-exchange crystallization. *Japanese Journal of Applied Physics*, **2014**, 53, 020302	1.4	13
154	Self-Organized Travelling-Zone-Melting Growth of a-Ge/Sn/c-Ge Stacked-Structures for High-Quality GeSn. *ECS Journal of Solid State Science and Technology*, **2014**, 3, P340-P343	2	1
153	Nucleation-controlled gold-induced-crystallization for selective formation of Ge(100) and (111) on insulator at low-temperature (~250 °C). *Applied Physics Letters*, **2013**, 103, 082102	3.4	60
152	Low-temperature crystallization of amorphous silicon and amorphous germanium by soft X-ray irradiation. *Thin Solid Films*, **2013**, 534, 334-340	2.2	12
151	High-quality formation of multiply stacked SiGe-on-insulator structures by temperature-modulated successive rapid-melting-growth. *Applied Physics Letters*, **2013**, 102, 092102	3.4	13
150	Crystallization of Electrodeposited Germanium Thin Film on Silicon (100). *Materials*, **2013**, 6, 5047-5057	3.5	10
149	Formation of Graded SiGe on Insulator by Segregation-Controlled Rapid-Melting-Growth. *ECS Transactions*, **2013**, 50, 747-751	1	
148	Low Temperature (~300°C) Epitaxial Growth of SiGe by Liquid-Solid Coexisting Annealing of A-GeSn/Si(100) Structure. *Applied Mechanics and Materials*, **2013**, 481, 137-140	0.3	
147	Atomically-Coherent-Coalescence of Two Growth-Fronts in Ge Stripes on Insulator by Rapid-Melting Lateral-Crystallization. *ECS Journal of Solid State Science and Technology*, **2013**, 2, P54-P57	2	1
146	Laterally-Graded Doping into Ge-on-Insulator by Combination of Ion-Implantation and Rapid-Melting Growth. *ECS Solid State Letters*, **2013**, 2, P58-P60		5
145	Formation of Giant SiGe Crystals on Insulator by Self-Organized-Seeding Rapid-Melting Growth. *Applied Mechanics and Materials*, **2013**, 481, 27-29	0.3	
144	Formation of Large Grain SiGe on Insulator by Si Segregation in Seedless-Rapid-Melting Process. *ECS Transactions*, **2013**, 50, 431-436	1	
143	(Invited) Low-Temperature Metal-Induced Crystallization of Orientation-Controlled SiGe on Insulator for Flexible Electronics. *ECS Transactions*, **2013**, 58, 213-221	1	
142	Liquid-Solid Coexisting Annealing of a-GeSn/Si(100) Structure for Low Temperature Epitaxial Growth of SiGe. *ECS Transactions*, **2013**, 58, 257-262	1	
141	Effects of dose on activation characteristics of P in Ge. *Thin Solid Films*, **2012**, 520, 3255-3258	2.2	0
140	Low temperature (~250°C) layer exchange crystallization of Si1−xGex (x=1−0) on insulator for advanced flexible devices. *Thin Solid Films*, **2012**, 520, 3293-3295	2.2	20
139	Enhancement of SiN-induced compressive and tensile strains in Si free-standing microstructures by modulation of SiN network structures. *Thin Solid Films*, **2012**, 520, 3276-3278	2.2	2

138	Self organization of FeGe/FeSi/FeGe layered structures on Ge and their electrical conduction properties. *Physics Procedia*, **2012**, 23, 21-24		1
137	Nano-lithography free formation of high density Ge-on-insulator network for epitaxial template. *Applied Physics Letters*, **2012**, 100, 092111	3.4	5
136	Enhanced Interfacial-Nucleation in Al-Induced Crystallization for (111) Oriented Si1−xGex(0≤x≤1) Films on Insulating Substrates. *ECS Journal of Solid State Science and Technology*, **2012**, 1, P144-P147	2	44
135	Epitaxial-Template Structure Utilizing Ge-on-Insulator Stripe Arrays with Nanospacing for Advanced Heterogeneous Integration on Si Platform. *Japanese Journal of Applied Physics*, **2012**, 51, 06FF04	1.4	6
134	Growth-rate-dependent laterally graded SiGe profiles on insulator by cooling-rate controlled rapid-melting-growth. *Applied Physics Letters*, **2012**, 101, 241904	3.4	17
133	Single-crystalline laterally graded GeSn on insulator structures by segregation controlled rapid-melting growth. *Applied Physics Letters*, **2012**, 101, 091905	3.4	26
132	Hybrid-orientation Ge-on-insulator structures on (100) Si platform by Si micro-seed formation combined with rapid-melting growth. *Applied Physics Letters*, **2012**, 100, 172107	3.4	21
131	Epitaxial-Template Structure Utilizing Ge-on-Insulator Stripe Arrays with Nanospacing for Advanced Heterogeneous Integration on Si Platform. *Japanese Journal of Applied Physics*, **2012**, 51, 06FF04	1.4	
130	Growth-Direction Dependent Rapid-Melting-Growth of Ge-On-Insulator (GOI) and its Application to Ge Mesh-Growth. *ECS Transactions*, **2011**, 35, 55-60	1	1
129	Ion channeling study of epitaxy of iron based Heusler alloy films on Ge(111). *Thin Solid Films*, **2011**, 519, 8461-8467	2.2	4
128	Source□Drain Engineering Using Atomically Controlled Heterojunctions for Next-Generation SiGe Transistor Applications. *Japanese Journal of Applied Physics*, **2011**, 50, 010101	1.4	34
127	Magnetooptical properties of iron based Heusler alloy epitaxial films on Ge(111). *Physics Procedia*, **2011**, 11, 200-203		8
126	Al-Induced oriented-crystallization of Si films on quartz and its application to epitaxial template for Ge growth. *Solid-State Electronics*, **2011**, 60, 7-12	1.7	26
125	Strained single-crystal GOI (Ge on Insulator) arrays by rapid-melting growth from Si (111) micro-seeds. *Solid-State Electronics*, **2011**, 60, 22-25	1.7	1
124	Growth-direction-dependent characteristics of Ge-on-insulator by Si□Ge mixing triggered melting growth. *Solid-State Electronics*, **2011**, 60, 18-21	1.7	2
123	Chip-size formation of high-mobility Ge strips on SiN films by cooling rate controlled rapid-melting growth. *Applied Physics Letters*, **2011**, 99, 032103	3.4	42
122	Single-crystalline (100) Ge networks on insulators by rapid-melting growth along hexagonal mesh-pattern. *Applied Physics Letters*, **2011**, 98, 042101	3.4	18
121	Mesh-shape-and-size controlled rapid-melting growth for the formation of single-crystalline (100), (110), and (111) Ge networks on insulators. *Applied Physics Letters*, **2011**, 98, 182107	3.4	12

120	Selective-mapping of uniaxial and biaxial strains in Si-on-insulator microstructures by polarized microprobe Raman spectroscopy. *Applied Physics Letters*, **2011**, 98, 012110	3.4	11
119	SiGe-Mixing-Triggered Rapid-Melting-Growth of High-Mobility Ge-On-Insulator. *Key Engineering Materials*, **2011**, 470, 8-13	0.4	5
118	Au-Catalyst Induced Low Temperature (~250 °C) Layer Exchange Crystallization for SiGe On Insulator. *ECS Transactions*, **2011**, 35, 39-42	1	3
117	Low-Temperature (~ 250°C) Cu-Induced Lateral Crystallization of Amorphous Ge on Insulator. *Electrochemical and Solid-State Letters*, **2011**, 14, H274		27
116	Dehydrogenation-Enhanced Large Strain (1.6%) in Si Pillars Covered by Si3N4 Stress Liners. *Electrochemical and Solid-State Letters*, **2011**, 14, H174-H176		2
115	Au-Induced Low-Temperature (~250°C) Crystallization of Si on Insulator Through Layer-Exchange Process. *Electrochemical and Solid-State Letters*, **2011**, 14, H232		25
114	Open-gated pH sensor fabricated on an undoped-AlGaN/GaN HEMT structure. *Sensors*, **2011**, 11, 3067-77	3.8	29
113	Source□Drain Engineering Using Atomically Controlled Heterojunctions for Next-Generation SiGe Transistor Applications. *Japanese Journal of Applied Physics*, **2011**, 50, 010101	1.4	16
112	High Quality Single-Crystalline Ge-Rich SiGe on Insulator Structures by Si-Doping Controlled Rapid Melting Growth. *Applied Physics Express*, **2010**, 3, 031301	2.4	16
111	Relaxation Mechanism of SiGe-on-Insulator by Oxidation-Induced Ge Condensation with H[sup +] Irradiation and Postannealing. *Journal of the Electrochemical Society*, **2010**, 157, H991	3.9	1
110	Effect of atomically controlled interfaces on Fermi-level pinning at metal/Ge interfaces. *Applied Physics Letters*, **2010**, 96, 162104	3.4	64
109	Microscopic studies of metal-induced lateral crystallization in SiGe. *Applied Physics Letters*, **2010**, 96, 182101	3.4	5
108	Defect-free Ge-on-insulator with (100), (110), and (111) orientations by growth-direction-selected rapid-melting growth. *Applied Physics Letters*, **2010**, 97, 152101	3.4	16
107	OPTICAL AND ELECTRONIC PROPERTIES OF M2Si (M = Mg, Ca, Sr) GROWN BY REACTIVE DEPOSITION TECHNIQUE. *International Journal of Modern Physics B*, **2010**, 24, 3693-3699	1.1	10
106	High-Hole-Mobility Single-Crystalline Ge Thin Films Formed on Insulating Substrates by SiGe Mixing-Triggered Directional Melting Growth. *Japanese Journal of Applied Physics*, **2010**, 49, 04DA08	1.4	5
105	(100) Orientation-Controlled Ge Giant-Stripes on Insulating Substrates by Rapid-Melting Growth Combined with Si Micro-Seed Technique. *Applied Physics Express*, **2010**, 3, 075603	2.4	17
104	Giant growth of single crystalline Ge on insulator by seeding lateral liquid-phase epitaxy. *Thin Solid Films*, **2010**, 518, S170-S173	2.2	12
103	Al-induced low-temperature crystallization of Si1□e (0 . *Thin Solid Films*, **2010**, 518, S174-S178	2.2	9

102	Formation of single-crystalline Ge stripes on quartz substrates by SiGe mixing-triggered liquid-phase epitaxy. *Thin Solid Films*, **2010**, 518, S179-S181	2.2	4
101	Liquid-phase epitaxial growth of Ge island on insulator using Ni-imprint-induced Si crystal as seed. *Thin Solid Films*, **2010**, 518, S182-S185	2.2	
100	Molecular beam epitaxial growth of ferromagnetic Heusler alloys for group-IV semiconductor spintronic devices. *Thin Solid Films*, **2010**, 518, S273-S277	2.2	10
99	Epitaxial growth of a full-Heusler alloy Co2FeSi on silicon by low-temperature molecular beam epitaxy. *Thin Solid Films*, **2010**, 518, S278-S280	2.2	16
98	Defect-free single-crystal Ge island arrays on insulator by rapid-melting-growth combined with seed-positioning technique. *Applied Physics Letters*, **2009**, 95, 112107	3.4	21
97	High-quality single-crystal Ge stripes on quartz substrate by rapid-melting-growth. *Applied Physics Letters*, **2009**, 95, 022115	3.4	67
96	Indentation-induced low-temperature solid-phase crystallization of Si1−xGex (x=0–1) on insulator. *Applied Physics Letters*, **2009**, 94, 192106	3.4	19
95	Stress-enhancement in free-standing Si pillars through nonequilibrium dehydrogenation in SiN:H stress-liners by ultraviolet light irradiation. *Applied Physics Letters*, **2009**, 95, 262103	3.4	2
94	Interfacial-Oxide Layer Controlled Al-Induced Crystallization of Si1-xGex(x: 0–1) on Insulating Substrate. *Japanese Journal of Applied Physics*, **2009**, 48, 03B002	1.4	29
93	Position-Controlled Growth of SiGe Crystal Grains on Insulator by Indentation-Induced Solid-Phase Crystallization. *Japanese Journal of Applied Physics*, **2009**, 48, 03B007	1.4	2
92	Effects of Si Layer Thickness on Solid-Phase Crystallization of Stacked Ge/Si/SiO2Structures. *Japanese Journal of Applied Physics*, **2009**, 48, 03B004	1.4	3
91	Electrical properties of poly-Ge on glass substrate grown by two-step solid-phase crystallization. *Solid-State Electronics*, **2009**, 53, 1159-1164	1.7	116
90	Orientation-controlled Si thin films on insulating substrates by Al-induced crystallization combined with interfacial-oxide layer modulation. *Applied Physics Letters*, **2009**, 95, 132103	3.4	103
89	Electrical injection and detection of spin-polarized electrons in silicon through an Fe3Si/Si Schottky tunnel barrier. *Applied Physics Letters*, **2009**, 94, 182105	3.4	113
88	Magnetic properties of epitaxially grown Fe3Si/Ge(111) layers with atomically flat heterointerfaces. *Journal of Applied Physics*, **2009**, 105, 07B102	2.5	37
87	Epitaxial ferromagnetic Fe3Si/Si(111) structures with high-quality heterointerfaces. *Applied Physics Letters*, **2008**, 93, 132117	3.4	79
86	Low-temperature molecular beam epitaxy of a ferromagnetic full-Heusler alloy Fe2MnSi on Ge(111). *Applied Physics Letters*, **2008**, 93, 112108	3.4	36
85	Nucleation-Controlled Metal-Induced Lateral Crystallization of Amorphous Si1-xGexwith Whole Ge Fraction on Insulator. *Japanese Journal of Applied Physics*, **2008**, 47, 1876-1879	1.4	6

84	Abnormal oxidation characteristics of SiGeSi-on-insulator structures depending on piled-up Ge fraction at SiO2SiGe interface. *Journal of Applied Physics*, **2008**, 103, 054909	2.5	2
83	Influences of Si pillar geometry on SiN-stressor induced local strain. *Applied Surface Science*, **2008**, 254, 6226-6228	6.7	6
82	Low-temperature solid-phase crystallization of amorphous SiGe films on glass by imprint technique. *Solid-State Electronics*, **2008**, 52, 1221-1224	1.7	2
81	Local strain evaluation of single crystal Si pillar by micro Raman spectroscopy and photoluminescence. *Thin Solid Films*, **2008**, 517, 31-33	2.2	1
80	Comprehensive study of low temperature (. *Thin Solid Films*, **2008**, 517, 251-253	2.2	5
79	Stress-relaxation mechanism in ultra-thin SiGe on insulator formed by H+ irradiation-assisted Ge condensation method. *Thin Solid Films*, **2008**, 517, 248-250	2.2	1
78	Atomically controlled hetero-epitaxy of Fe3Si/SiGe for spintronics application. *Thin Solid Films*, **2008**, 517, 181-183	2.2	6
77	Low-temperature oriented growth in [CoPt/MgO]n multi-layer. *Thin Solid Films*, **2008**, 517, 430-433	2.2	
76	Temperature dependent epitaxial growth of ferromagnetic silicide Fe3Si on Ge substrate. *Thin Solid Films*, **2008**, 517, 422-424	2.2	4
75	Low temperature epitaxial growth of Fe3Si on Si(111) substrate through ultra-thin SiO2 films. *Thin Solid Films*, **2008**, 517, 425-427	2.2	4
74	Low temperature formation of multi-layered structures of ferromagnetic silicide Fe3Si and Ge. *Applied Surface Science*, **2008**, 254, 6215-6217	6.7	14
73	Influence of substrate orientation on low-temperature epitaxial growth of ferromagnetic silicide Fe3Si on Si. *Thin Solid Films*, **2007**, 515, 8250-8253	2.2	11
72	Ge-Channel Thin-Film Transistor with Schottky Source/Drain Fabricated by Low-Temperature Processing. *Japanese Journal of Applied Physics*, **2007**, 46, 1250-1253	1.4	15
71	Ni-imprint induced solid-phase crystallization in Si1−xGex (x: 0–1) on insulator. *Applied Physics Letters*, **2007**, 91, 042111	3.4	56
70	Axial orientation of molecular-beam-epitaxy-grown Fe3SiGe hybrid structures and its degradation. *Applied Physics Letters*, **2007**, 91, 171910	3.4	29
69	Improved Oxidation-Induced Ge Condensation Technique Using H+Implantation and Post Annealing for Highly Stress-Relaxed Ultrathin SiGe on Insulator. *Japanese Journal of Applied Physics*, **2006**, 45, 3147-3149	1.4	2
68	Suppression of Floating Body Effects in Polycrystalline Silicon Thin-Film Transistor by Schottky Source/Drain Structure. *Japanese Journal of Applied Physics*, **2006**, 45, 4370-4373	1.4	3
67	Electric-Field-Assisted Metal-Induced Lateral Crystallization of Amorphous SiGe on SiO2. *Japanese Journal of Applied Physics*, **2006**, 45, 4351-4354	1.4	10

66	Temperature dependent metal-induced lateral crystallization of amorphous SiGe on insulating substrate. *Applied Physics Letters*, **2006**, 89, 182120	3.4	64
65	Low-temperature formation (. *Applied Physics Letters*, **2006**, 89, 192114	3.4	85
64	Highly strain-relaxed ultrathin SiGe-on-insulator structure by Ge condensation process combined with H+ irradiation and postannealing. *Applied Physics Letters*, **2006**, 88, 142105	3.4	16
63	Epitaxial Growth of Ferromagnetic Silicide Fe3Si on Si(111) Substrate. *Japanese Journal of Applied Physics*, **2006**, 45, 3598-3600	1.4	22
62	Atomically controlled molecular beam epitaxy of ferromagnetic silicide Fe3Si on Ge. *Applied Physics Letters*, **2006**, 89, 182511	3.4	46
61	??????????SiGe???????. *Materia Japan*, **2006**, 45, 725-728	0.1	
60	Characterization of metal-induced lateral crystallization of amorphous SiGe on insulating film. *Thin Solid Films*, **2006**, 508, 57-60	2.2	6
59	Electric field-dependent Ni-mediated lateral crystallization of a-Si on SiO2. *Thin Solid Films*, **2006**, 508, 40-43	2.2	2
58	Thickness-dependent stress-relaxation in thin SGOI structures and its improvement. *Thin Solid Films* , **2006**, 508, 247-250	2.2	8
57	Au-induced lateral crystallization of a-Si1−xGex (x: 0−1) at low temperature. *Thin Solid Films*, **2006**, 508, 44-47	2.2	17
56	Morphological change of Co-nanodot on SiO2 by thermal treatment. *Thin Solid Films*, **2006**, 508, 178-181	2.2	
55	Low-Temperature Formation of Poly-Si1-xGex (0≤x≤1) Films by Ni-Induced Lateral Crystallization for Advanced TFT. *IEEJ Transactions on Electronics, Information and Systems*, **2006**, 126, 1073-1078	0.1	
54	H+ implantation-enhanced stress relaxation in c-Si1−xGex on SiO2 during oxidation-induced Ge condensation process. *Materials Science in Semiconductor Processing*, **2005**, 8, 167-170	4.3	0
53	Ge-enhanced MILC velocity in a-Ge/a-Si/SiO2 layered structure. *Materials Science in Semiconductor Processing*, **2005**, 8, 83-88	4.3	5
52	400 °C Formation of poly-SiGe on SiO2 by Au-induced lateral crystallization. *Materials Science in Semiconductor Processing*, **2005**, 8, 79-82	4.3	7
51	Pulsed laser crystallization of silicon–germanium films. *Thin Solid Films*, **2005**, 487, 67-71	2.2	18
50	Directional Growth of Si Nanowires on Insulating Films by Electric-Field-Assisted Metal-Induced Lateral Crystallization. *Materials Research Society Symposia Proceedings*, **2005**, 891, 1		2
49	Improvement of Oxidation-Induced Ge Condensation Method by H+Implantation and Two-Step Annealing for Highly Stress-Relaxed SiGe-on-Insulator. *Japanese Journal of Applied Physics*, **2005**, 44, 2357-2360	1.4	4

48	Low-Temperature Formation of Poly-Si1-xGex(x: 0□1) on SiO2by Au-Mediated Lateral Crystallization. *Japanese Journal of Applied Physics*, **2005**, 44, 2405-2408	1.4	7
47	Enhanced stress relaxation in ultrathin SiGe-on-insulator by H+-implantation-assisted oxidation. *Applied Physics Letters*, **2005**, 86, 211901	3.4	13
46	Ge fraction dependent improved thermal stability of in situ doped boron in polycrystalline Si1□Gex (0?x?0.5) films on SiON. *Journal of Applied Physics*, **2005**, 97, 054909	2.5	11
45	Ion-Beam Enhanced Stress-Relaxation of SiGe on SiO2. *Materials Research Society Symposia Proceedings*, **2005**, 908, 1		
44	Formation of □FeSi2-xGexby Ge-Segregation-Controlled Solid-Phase Growth of [a-Si/a-FeSiGe]nMultilayered Structure. *Japanese Journal of Applied Physics*, **2004**, 43, 1879-1881	1.4	2
43	Nucleation Control in Solid-Phase Crystallization of a-Si/SiO2by Local Ge Insertion. *Japanese Journal of Applied Physics*, **2004**, 43, 1901-1904	1.4	8
42	Modified metal-induced lateral crystallization using amorphous Ge□Si layered structure. *Applied Physics Letters*, **2004**, 85, 899-901	3.4	14
41	Solid-phase crystallization of high-quality Si films on SiO2 by local Ge-insertion. *Thin Solid Films*, **2004**, 451-452, 489-492	2.2	5
40	Enhancement of metal-induced crystallization in Ge/Si/Ni/SiO2 layered structure. *Thin Solid Films*, **2004**, 451-452, 324-327	2.2	3
39	Solid-phase crystallization of □FeSi2 thin film in Fe/Si structure. *Thin Solid Films*, **2004**, 461, 68-71	2.2	6
38	Formation of SiGe/□FeSi2 superstructures from amorphous Si/FeSiGe layers. *Thin Solid Films*, **2004**, 461, 77-80	2.2	1
37	Impurity conduction in ion beam synthesized □FeSi2/Si. *Thin Solid Films*, **2004**, 461, 198-201	2.2	3
36	Enhanced crystal nucleation in a-Si on SiO2 by local Ge doping. *Thin Solid Films*, **2004**, 464-465, 99-102	2.2	4
35	Ge-dependent morphological change in poly-SiGe formed by Ni-mediated crystallization. *Applied Surface Science*, **2004**, 224, 227-230	6.7	8
34	Enhanced crystal nucleation in a-SiGe/SiO2 by ion-irradiation assisted annealing. *Applied Surface Science*, **2004**, 224, 231-234	6.7	24
33	Electrical and structural properties of poly-SiGe film formed by pulsed-laser annealing. *Journal of Applied Physics*, **2004**, 95, 6457-6461	2.5	53
32	Metal-Induced Solid-Phase Crystallization of Amorphous SiGe Films on Insulator. *Japanese Journal of Applied Physics*, **2003**, 42, 1933-1936	1.4	15
31	Etching characteristics of SiO2 irradiated with focused ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 478-481	1.2	9

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29	Relaxation process of ion irradiation defects in IV-semiconductors. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **2003**, 102, 362-365	3.1	
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